2N3906A

EPITAXIAL PLANAR PNP TRANSISTOR

GENERAL PURPOSE APPLICATION.
SWITCHING APPLICATION.

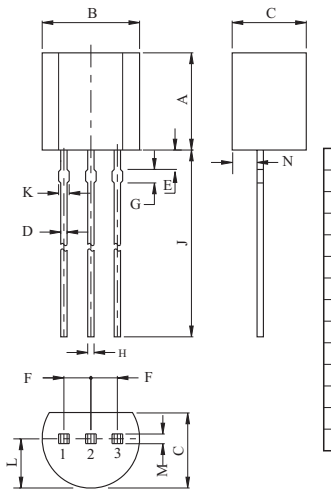
FEATURES

· Low Leakage Current
: I_{CEX}=-50nA(Max.), I_{BL}=-50nA(Max.)
@V_{CE}=-30V, V_{EB}=-3V.

· Low Saturation Voltage
: $V_{CE(sat)}$=-0.4V(Max.) @I_C=-50mA, I_B=-5mA.

· Low Collector Output Capacitance
: C_{ob}=4.5pF(Max.) @V_{CB}=5V.

· Complementary to 2N3904A.



DIM	MILLIMETERS
A	4.70 MAX
B	4.80 MAX
C	3.70 MAX
D	0.45
E	1.00
F	1.27
G	0.85
H	0.45
J	14.00±0.50
K	0.55 MAX
L	2.30
M	0.45 MAX
N	1.00

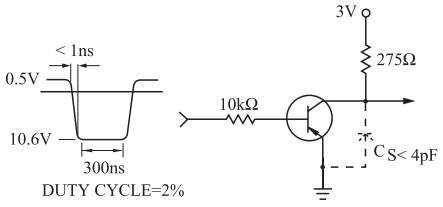
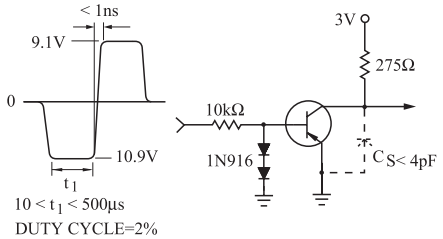
1. EMITTER
2. BASE
3. COLLECTOR

TO-92

MAXIMUM RATING (Ta=25℃)

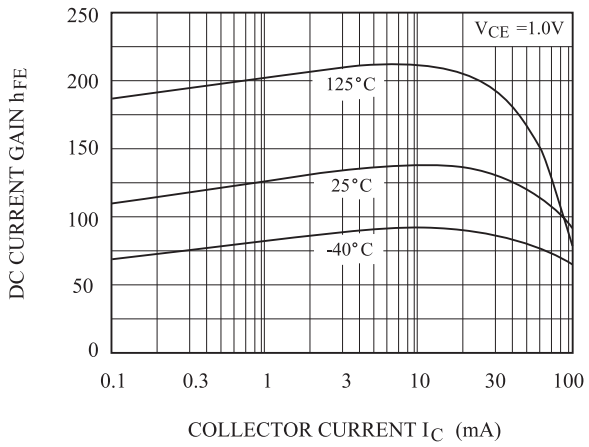
CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	-40	V
Collector-Emitter Voltage		V_{CEO}	-40	V
Emitter-Base Voltage		V_{EBO}	-5	V
Collector Current		I_C	-200	mA
Base Current		I_B	-50	mA
Collector Power Dissipation	Ta=25℃	P_C	625	mW
	Tc=25℃		1.5	W
Junction Temperature		T_j	150	℃
Storage Temperature Range		T_{stg}	-55～150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

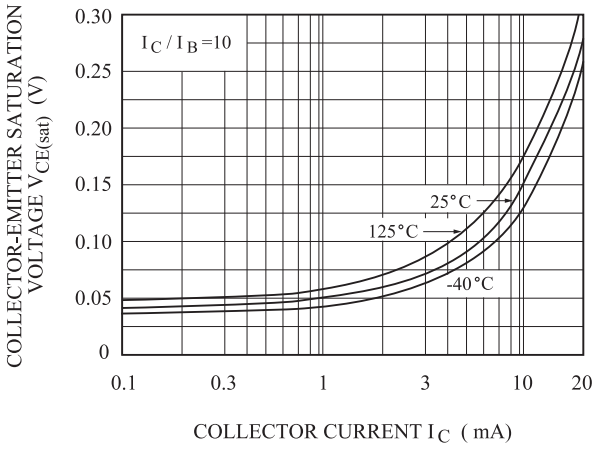
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CEX}	V_{CE}=-30V, V_{EB}=-3V	-	-	-50	nA
Base Cut-off Current		I_{BL}	V_{CE}=-30V, V_{EB}=-3V	-	-	-50	nA
Collector-Base Breakdown Voltage		$V_{(BR)CBO}$	I_C=-10μA, I_E=0	-40	-	-	V
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	I_C=-1mA, I_B=0	-40	-	-	V
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	I_E=-10μA, I_C=0	-5.0	-	-	V
DC Current Gain *		$h_{FE}(1)$	V_{CE}=-1V, I_C=-0.1mA	60	-	-	
		$h_{FE}(2)$	V_{CE}=-1V, I_C=-1mA	80	-	-	
		$h_{FE}(3)$	V_{CE}=-1V, I_C=-10mA	100	-	300	
		$h_{FE}(4)$	V_{CE}=-1V, I_C=-50mA	60	-	-	
		$h_{FE}(5)$	V_{CE}=-1V, I_C=-100mA	30	-	60	
Collector-Emitter Saturation Voltage *		$V_{CE(sat)}1$	I_C=-10mA, I_B=-1mA	-	-	-0.25	V
		$V_{CE(sat)}2$	I_C=-50mA, I_B=-5mA	-	-	-0.4	
Base-Emitter Saturation Voltage *		$V_{BE(sat)}1$	I_C=-10mA, I_B=-1mA	-0.65	-	-0.85	V
		$V_{BE(sat)}2$	I_C=-50mA, I_B=-5mA	-	-	-0.95	
Transition Frequency		f_T	V_{CE}=-20V, I_C=-10mA, f=100MHz	250	-	-	MHz
Collector Output Capacitance		C_{ob}	V_{CB}=-5V, I_E=0, f=1MHz	-	-	4.5	pF
Input Capacitance		C_{ib}	V_{BE}=-0.5V, I_C=0, f=1MHz	-	-	10	pF
Input Impedance		h_{ie}	V_{CE}=-10V, I_C=-1mA, f=1kHz	2.0	-	12	kΩ
Voltage Feedback Ratio		h_{re}		1.0	-	10	$x10^{-4}$
Small-Signal Current Gain		h_{fe}		100	-	400	
Collector Output Admittance		h_{oe}		3.0	-	60	μ℧
Noise Figure		NF	V_{CE}=-5V, I_C=-0.1mA, Rg=1kΩ, f=10Hz～15.7kHz	-	-	4.0	dB
Switching Time	Delay Time	t_d		-	-	35	nS
	Rise Time	t_r		-	-	35	
	Storage Time	t_{stg}		-	-	225	
	Fall Time	t_f		-	-	75	

* Pulse Test : Pulse Width≦300μS, Duty Cycle≦2%.

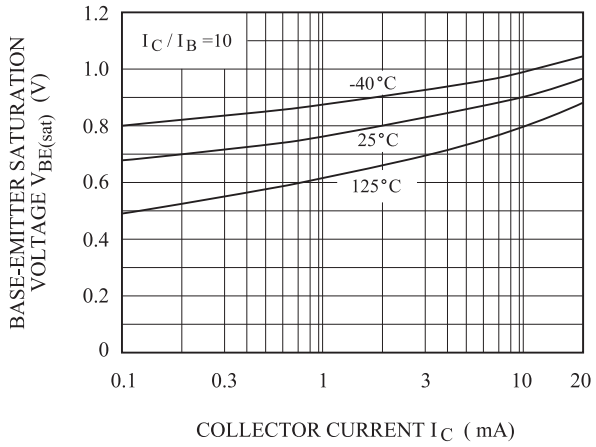
h_{FE} - I_C



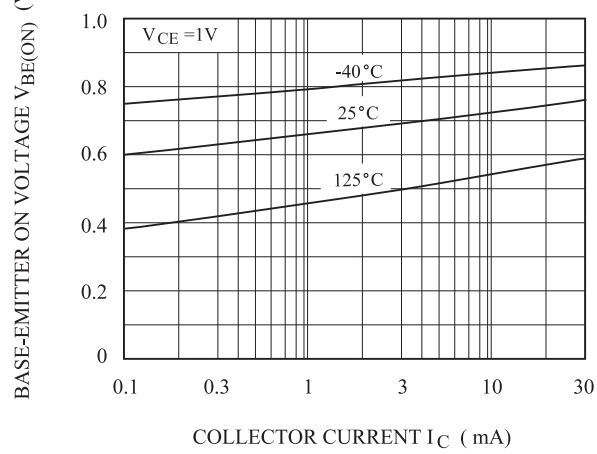
$V_{CE(sat)}$ - I_C



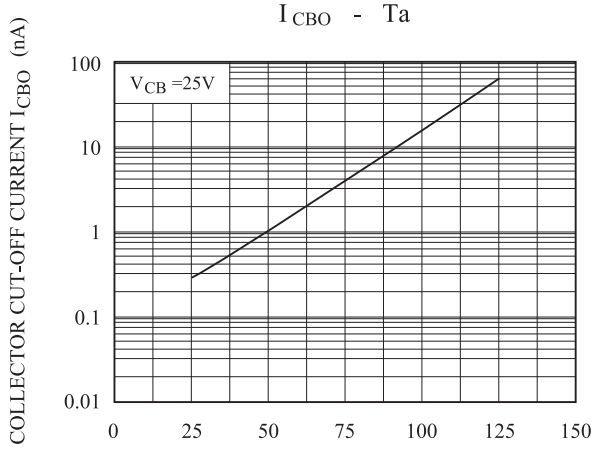
$V_{BE(sat)}$ - I_C



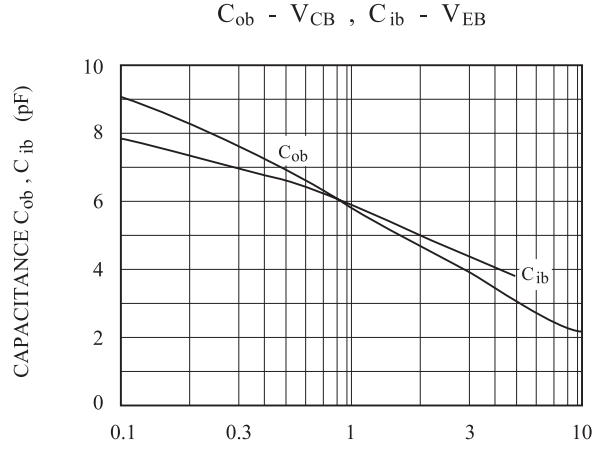
$V_{BE(ON)}$ - I_C



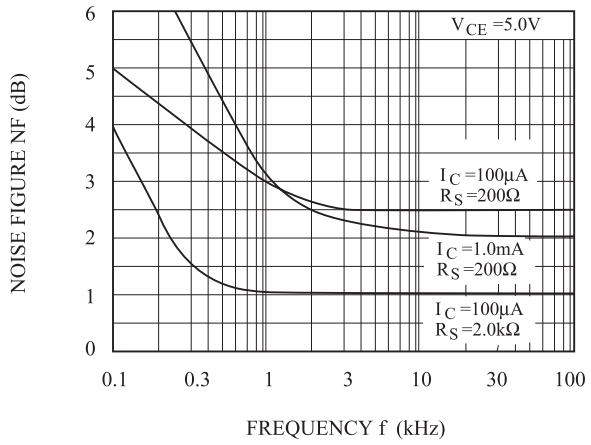
I_{CBO} - Ta



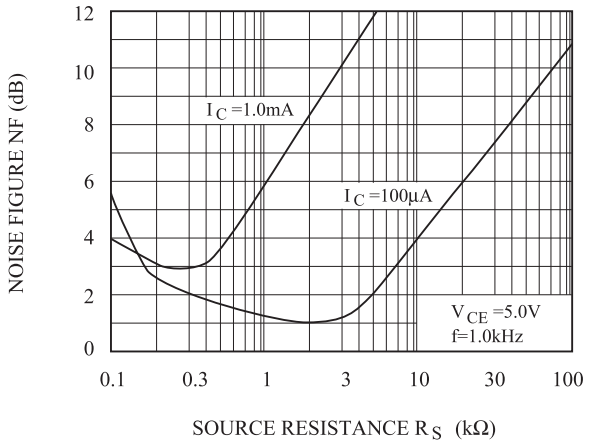
C_{ob} - V_{CB} , C_{ib} - V_{EB}



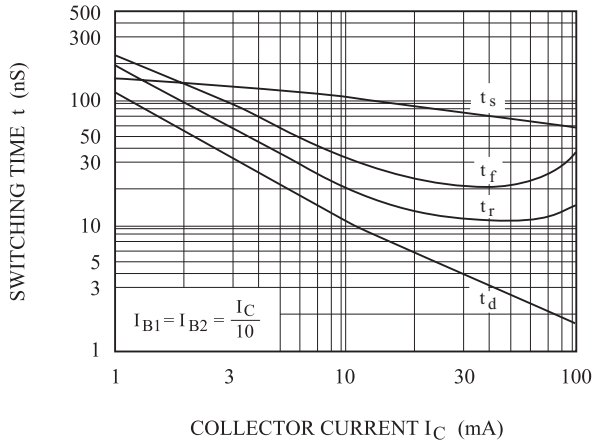
NF - f



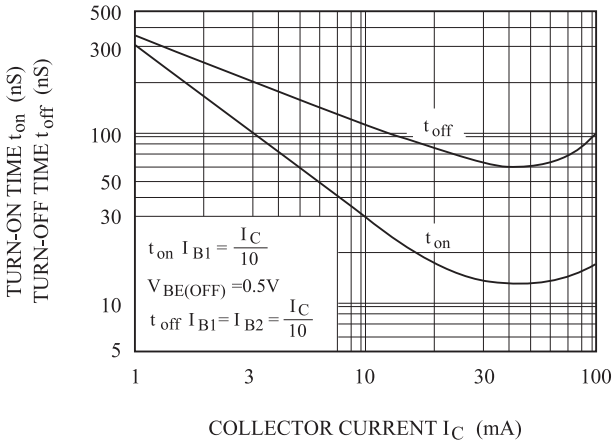
NF - R_S



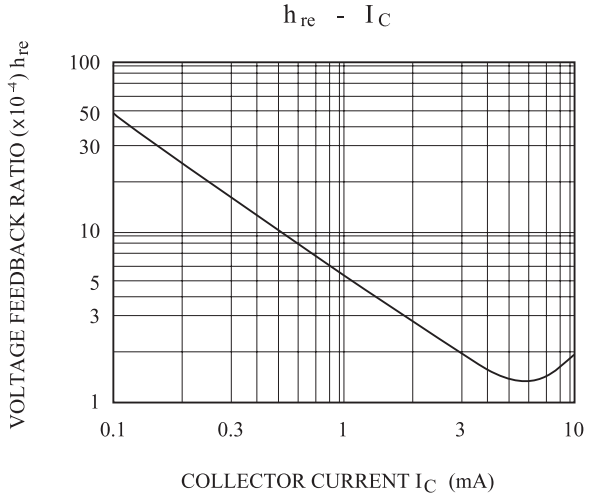
t - I_C



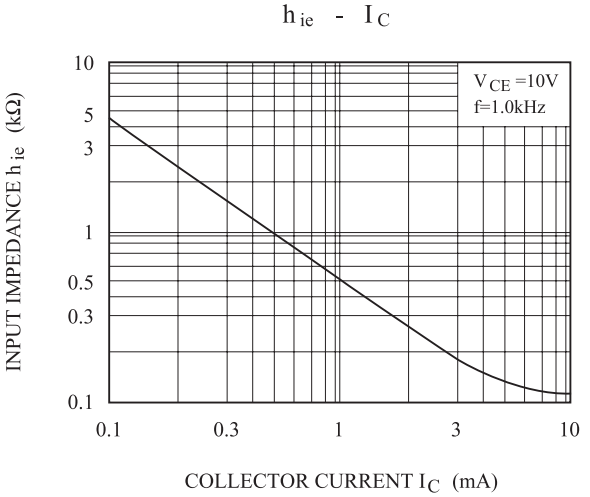
t_{on} - I_C , t_{off} - I_C



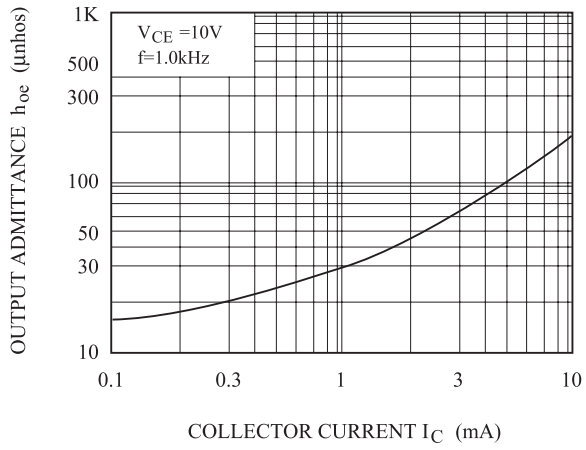
h_{re} - I_C



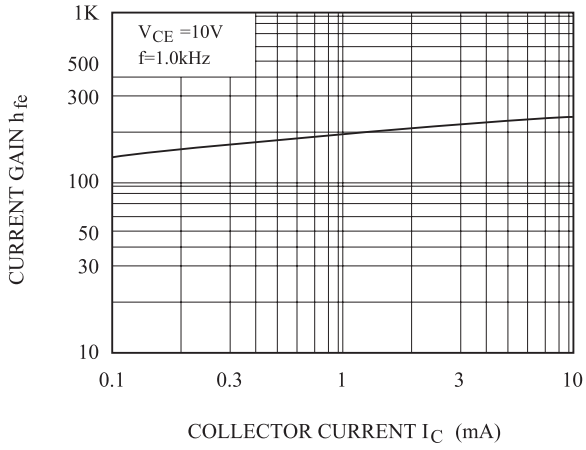
h_{ie} - I_C



h_{oe} - I_C



h_{fe} - I_C



Pc - Ta